SUBJECT AREAS:
SPINTRONICS
ELECTRONIC DEVICES

CORRIGENDUM: Room temperature electrical spin injection into GaAs by an oxide spin injector

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The following sentence was inaccurate and has been removed from the abstract: “So far there is no success in using a magnetic oxide material for spin injection, which is very important for the development of oxide based spintronics devices.”

The following sentence in the introduction was inaccurate: “From earlier reports it is seen that spin injection using in-plane magnetized ferromagnetic systems in GaAs is observed only up to $\sim 120 \text{ K}^{2-4, 22, 23}$.” It has been changed to: “From earlier reports it is seen that all electrical spin injection and detection using in-plane magnetized ferromagnetic systems in GaAs is observed only up to $\sim 120 \text{ K}^{2-4, 22, 23}$.”